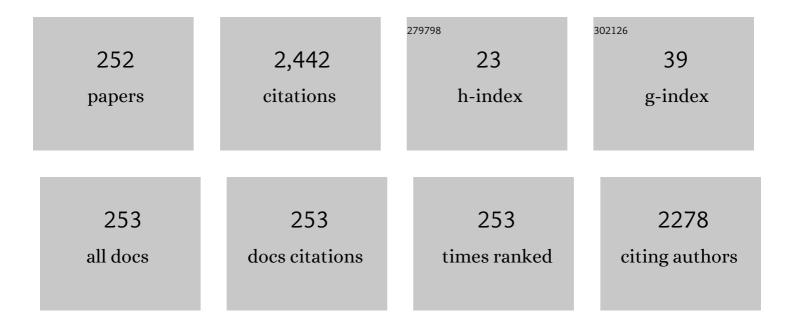
## Naoki Wakiya

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Preparation and characterization of epitaxially grown yttria-stabilized zirconia thin films on porous silicon substrates for solid oxide fuel cell applications. Journal of the Ceramic Society of Japan, 2022, 130, 464-470.	1.1	2
2	Molecular design effects of alkoxide-derived precursor solution on low-temperature crystallization of cubic garnet type Li ion conductor. Materials Letters, 2021, 283, 128747.	2.6	8
3	Enhanced Magnetoelectric Effects in Self-Assembled Hemispherical Close-Packed CoFe2O3-Pb(Zr0.52Ti0.48)O3 Thin Film. Journal of Electronic Materials, 2021, 50, 1699-1706.	2.2	4
4	Magnetoelectric Studies of Close-Packed and Hierarchically Ordered CoFe2O4/Pb(Zr0.52Ti0.48)O3/La0.6Sr0.4MnO3/LaNiO3 Multiferroic Thin Films. Journal of Electronic Materials, 2021, 50, 1678-1685.	2.2	2
5	Magnetic and Mechanical Properties of Iron-Based Soft Magnetic Composites Coated with Silane Synergized by Bi2O3. Journal of Electronic Materials, 2021, 50, 2425-2435.	2.2	7
6	As-grown Mn <sub>3</sub> CuN thin films with high crystallinity prepared by dynamic aurora pulsed laser deposition. Journal of the Ceramic Society of Japan, 2021, 129, 377-382.	1.1	1
7	Development of dynamic aurora pulsed laser deposition equipped with reflection high-energy electron diffraction and effects of magnetic fields on room-temperature epitaxial growth of NiO thin film. Journal of the Ceramic Society of Japan, 2021, 129, 343-347.	1.1	1
8	Spontaneous superlattice formation and electrical properties of Sr-excess SrTiO <sub>3</sub> thin film deposited on SrTiO <sub>3</sub> (101) by dynamic aurora pulsed laser deposition. Journal of the Ceramic Society of Japan, 2021, 129, 390-396.	1.1	2
9	Dynamic Aurora PLD with Si and porous Si to prepare ZnFe <sub>2</sub> 0 <sub>4</sub> Thin films for liquefied petroleum gas sensing. Journal of the Ceramic Society of Japan, 2020, 128, 457-463.	1.1	2
10	Epitaxial growth of neodymia stabilized zirconia on Si(001) substrate using dynamic aurora PLD. Journal of the Ceramic Society of Japan, 2020, 128, 693-699.	1.1	1
11	Wide range lattice parameter control by aliovalent substitution to the rare-earth site in cubic garnet Li <sub>6.75</sub> (La <sub>1â^²</sub> <i><sub>x</sub></i> Sm <i><sub>x</sub></i> ) <sub>3</sub> Zr <sub>1.7 Journal of the Ceramic Society of Japan, 2020, 128, 700-705.</sub>	75< <b>/su</b> b≻Ta	a <sub>0.25</sub>
12	Preparation of flat cross section of thin films by perforation fracture method. Journal of the Ceramic Society of Japan, 2020, 128, 706-709.	1.1	0
13	Effect of deposition conditions and buffer layers on amorphous or polytype phase formation in Al <sub>2</sub> O <sub>3</sub> thin films by chemical vapor deposition using tri-methyl aluminum. Journal of the Ceramic Society of Japan, 2019, 127, 443-450.	1.1	1
14	Influence of Particle Size on the Spin Pinning Effect in the fcc-FePt Nanoparticles. Journal of Superconductivity and Novel Magnetism, 2019, 32, 1501-1505.	1.8	0
15	Superparamagnetic magnesium ferrite/silica core-shell nanospheres: A controllable SiO2 coating process for potential magnetic hyperthermia application. Advanced Powder Technology, 2019, 30, 3171-3181.	4.1	25
16	Interface structure of Pb(Zr,Ti)O3/MgO(001) epitaxial thin film in early stage of Stranski–Krastanov growth mode. Japanese Journal of Applied Physics, 2019, 58, SLLA08.	1.5	4
17	Properties of MgFe2O4 Nanoparticles Synthesized by Ultrasonic Aerosol Pyrolysis for Biomedical Applications. Physics of the Solid State, 2019, 61, 1113-1121.	0.6	4
18	Magnetoelectric effect in free-standing multiferroic thin film. Journal of Alloys and Compounds, 2019, 787, 1128-1135.	5.5	1

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19	Low temperature and fast growth of one-directionally grown aluminum nitride film by atmospheric pressure halide CVD method. Journal of the Ceramic Society of Japan, 2019, 127, 612-616.	1.1	2
20	Low-temperature processing of Garnet-type ion conductive cubic Li7La3Zr2O12 powders for high performance all solid-type Li-ion batteries. Journal of the Taiwan Institute of Chemical Engineers, 2018, 90, 85-91.	5.3	17
21	Preparation of free-standing multilayer hemispherical shell thin film using monodisperse polymer template. Journal of Alloys and Compounds, 2018, 730, 369-375.	5.5	3
22	Influence of crystallite size on the magnetic and heat generation properties of La0.77Sr0.23MnO3 nanoparticles for hyperthermia applications. Journal of Physics and Chemistry of Solids, 2018, 112, 179-184.	4.0	18
23	Controlled synthesis of dense MgFe2O4 nanospheres by ultrasonic spray pyrolysis technique: Effect of ethanol addition to precursor solvent. Advanced Powder Technology, 2018, 29, 283-288.	4.1	16
24	Magnetic-field-induced phase separation via spinodal decomposition in epitaxial manganese ferrite thin films. Science and Technology of Advanced Materials, 2018, 19, 507-516.	6.1	11
25	Cross Sectional Processing of Ferroelectric Thin Films by Ion-milling for AFM Analysis. Materia Japan, 2018, 57, 602-602.	0.1	1
26	As-grown enhancement of spinodal decomposition in spinel cobalt ferrite thin films by Dynamic Aurora pulsed laser deposition. Journal of Magnetism and Magnetic Materials, 2017, 432, 391-395.	2.3	13
27	Impact of precursor solution concentration to form superparamagnetic MgFe2O4 nanospheres by ultrasonic spray pyrolysis technique for magnetic thermotherapy. Advanced Powder Technology, 2017, 28, 1696-1703.	4.1	16
28	Preparation of (La1â^'xSrx)MnO3â^'δ thin films on Si (100) substrates by a metal-organic decomposition method for smart radiation devices. Thin Solid Films, 2017, 626, 154-158.	1.8	6
29	Charge screening strategy for domain pattern control in nano-scale ferroelectric systems. Scientific Reports, 2017, 7, 5236.	3.3	14
30	Progress and impact of magnetic field application during pulsed laser deposition (PLD) on ceramic thin films. Journal of the Ceramic Society of Japan, 2017, 125, 856-865.	1.1	15
31	Synthesis of Silica-Coated Magnetic Nanoparticles Using Acid Catalysis. Hosokawa Powder Technology Foundation ANNUAL REPORT, 2017, 25, 132-137.	0.0	Ο
32	Preparation and Analysis of New Phase of Calcium Aluminate Prepared by Solution Plasma Processing. Journal of the Society of Powder Technology, Japan, 2017, 54, 4-9.	0.1	1
33	Orientation control of SrRuO3 thin film on a Si substrate by chemical solution deposition for an electrode of lead zirconate titanate thin films. Materials Letters, 2016, 181, 74-77.	2.6	10
34	Magnetic-field-induced spontaneous superlattice formation via spinodal decomposition in epitaxial strontium titanate thin films. NPG Asia Materials, 2016, 8, e279-e279.	7.9	19
35	Effect of the reduction condition on the catalytic activity for steam reforming process using Ni doped LaAlO 3 nano-particles. Advanced Powder Technology, 2016, 27, 179-183.	4.1	9
36	Synthesis and electrical properties of Pb(Mg1/3Nb2/3)O3–PbTiO3 epitaxial thin films on Si wafers using chemical solution deposition. Thin Solid Films, 2016, 603, 97-102.	1.8	9

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37	Impact of acidic catalyst to coat superparamagnetic magnesium ferrite nanoparticles with silica shell via sol–gel approach. Advanced Powder Technology, 2016, 27, 541-549.	4.1	20
38	Catalytic Activities of Alkoxide-derived LaAlO <sub>3</sub> for Ethanol Steam Reforming Processing. Transactions of the Materials Research Society of Japan, 2015, 40, 51-54.	0.2	1
39	Effects of synthesis conditions on electrical properties of chemical solution deposition-derived Pb(Mg1/3Nb2/3)O3–PbTiO3 thin films. Thin Solid Films, 2015, 585, 86-90.	1.8	10
40	Investigations of superparamagnetism in magnesium ferrite nano-sphere synthesized by ultrasonic spray pyrolysis technique for hyperthermia application. Journal of Magnetism and Magnetic Materials, 2015, 392, 91-100.	2.3	55
41	Stress engineering for the design of morphotropic phase boundary in piezoelectric material. Thin Solid Films, 2015, 585, 91-94.	1.8	6
42	Thermal radiative properties of (La1â^'xSrx)MnO3â~'δ thin films fabricated on yttria-stabilized zirconia single-crystal substrate by pulsed laser deposition. Thin Solid Films, 2015, 593, 1-4.	1.8	7
43	Catalytic Activity for the Methane Steam Reforming Process Using Chemical Solution Deposition Derived Barium Titanate Hollow Particles with Perovskite Mono-phase. Journal of the Society of Powder Technology, Japan, 2014, 51, 337-342.	0.1	4
44	Low-temperature Synthesis of 12CaO • 7Al2O3 Particles by Solution Plasma Processing. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2014, 61, 93-98.	0.2	1
45	Fabrication of Vanadium Dioxide Nano-particles by Microemulsion Method with Controlled Phase Transition Temperatures. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2014, 61, 99-103.	0.2	2
46	Phase diagram and piezoelectric response of (Ba <sub>1â^'<i>x</i></sub> Ca <sub><i>x</i></sub> )(Zr <sub>0.1</sub> Ti <sub>0.9</sub> )O <sub>3</sub> solid solution. Journal of Physics Condensed Matter, 2013, 25, 425901.	1.8	18
47	Effects of Oxide Seeding Layers on Electrical Properties of Chemical Solution Deposition-Derived Pb(Mg1/3Nb2/3)O3–PbTiO3Relaxor Thin Films. Japanese Journal of Applied Physics, 2013, 52, 09KA07.	1.5	0
48	Stress state analysis of stress engineered BaTiO <sub>3</sub> thin film by LaNiO <sub>3</sub> bottom electrode. Journal of the Ceramic Society of Japan, 2013, 121, 273-277.	1.1	0
49	Effect of facing annealing on crystallization and decomposition of Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> thin films prepared by CSD technique using MOD solution. Journal of the Ceramic Society of Japan, 2013, 121, 236-241.	1.1	12
50	Magnetic and photocatalytic properties of n- and p-type ZnFe <sub>2</sub> O <sub>4</sub> particles synthesized using ultrasonic spray pyrolysis. Journal of the Ceramic Society of Japan, 2013, 121, 26-30.	1.1	13
51	Effect of facing annealing on crystallization and decomposition of Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> thin films prepared by CSD technique using MOD solution. Journal of the Ceramic Society of Japan, 2013, 121, 326-326.	1.1	0
52	Magnetic field effects during deposition on crystal structure and magnetic properties of BaFe <sub>12</sub> O <sub>19</sub> thin films prepared using PLD in the magnetic field (Dynamic aurora PLD). Journal of the Ceramic Society of Japan, 2013, 121, 45-48.	1.1	6
53	Micro/Crystal structure analysis of CSD derived porous LaNiO <sub>3</sub> electrode films. Journal of the Ceramic Society of Japan, 2013, 121, 619-622.	1.1	4
54	Effect of step edges on the growth of Pt thin films on oxide single-crystal substrates. Journal of the Ceramic Society of Japan, 2013, 121, 278-282.	1.1	1

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55	TEM MICROSTRUCTURE ANALYSIS FOR COMPRESSIVELY STRESSED <font>Pb(Zr,Ti)O<sub>3</sub></font> THIN FILMS BY CSD-DERIVED <font>LaNiO<sub>3</sub></font> BOTTOM ELECTRODES. Functional Materials Letters, 2012, 05, 1260016.	1.2	3
56	Strain-Induced Electrical Properties of Lead Zirconate Titanate Thin Films on a Si wafer with Controlled Oxide Electrode Structure. Japanese Journal of Applied Physics, 2012, 51, 09LA13.	1.5	5
57	<font>BaTiO<sub>3</sub></font> THIN FILM BY CSD FROM MOLECULAR-DESIGNED PRECURSOR SOLUTION. Functional Materials Letters, 2012, 05, 1260007.	1.2	1
58	Low temperature processing of alkoxide-derived PMN thin films. IOP Conference Series: Materials Science and Engineering, 2012, 30, 012002.	0.6	3
59	Effect of Thermal Stress on Orientation Control of <scp>CSD</scp> â€Derived <scp><scp>Pb(Zr<sub>0.53</sub>Ti<sub>0.47</sub>)O<sub>3</sub></scp></scp> Thin Films. International Journal of Applied Ceramic Technology, 2012, 9, 868-875.	2.1	9
60	Strain-Induced Electrical Properties of Lead Zirconate Titanate Thin Films on a Si wafer with Controlled Oxide Electrode Structure. Japanese Journal of Applied Physics, 2012, 51, 09LA13.	1.5	3
61	Low-temperature Synthesis of Functional Oxide Nanopowders by Sol-Gel method from Molecular-designed Metal Alkoxides. Journal of the Society of Powder Technology, Japan, 2012, 49, 378-389.	0.1	1
62	Fabrication of 12CaO 7Al2O3 powders with high specific surface area by sol-gel and ball-milling method. Journal of the Ceramic Society of Japan, 2011, 119, 460-463.	1.1	12
63	Microstructure and electrical properties of BaTiO3 thin films by modified CSD. Journal of the Ceramic Society of Japan, 2011, 119, 498-501.	1.1	4
64	Fabrication of transition temperature controlled W-doped VO2 nano particles by aqueous solution. Journal of the Ceramic Society of Japan, 2011, 119, 522-524.	1.1	9
65	Synthesis and hyperthermia property of hydroxyapatite–ferrite hybrid particles by ultrasonic spray pyrolysis. Journal of Magnetism and Magnetic Materials, 2011, 323, 965-969.	2.3	53
66	Preparation of heteroepitaxial SrRuO3 thin film on Si substrate and microstructure of BaTiO3-NiFe2O4 epitaxial composite thin film deposited on the SrRuO3 bottom electrode using PLD. Materials Research Society Symposia Proceedings, 2011, 1308, 71201.	0.1	0
67	Ferroelectricity of SrTiO <sub>3</sub> Thin Films Prepared by Dynamic-Aurora Pulsed Laser Deposition. Key Engineering Materials, 2011, 485, 11-14.	0.4	1
68	Fabrication of two-dimensional close-packed shell structure in ceramic thin films. Science and Technology of Advanced Materials, 2011, 12, 034405.	6.1	3
69	Magnetic and optical properties of MgAl2O4-(Ni0.5Zn0.5)Fe2O4thin films prepared by pulsed laser deposition. Science and Technology of Advanced Materials, 2011, 12, 034408.	6.1	5
70	Effect of Stress Engineering on the Electrical Properties of BaTiO\$_{3}\$ Thin Film. Japanese Journal of Applied Physics, 2011, 50, 09NA03.	1.5	12
71	Magnetic Properties of Epitaxial NiFe <sub>2</sub> O <sub>4</sub> Thin Films Prepared Using Dynamic Aurora PLD in a Magnetic Field. Key Engineering Materials, 2011, 485, 221-224.	0.4	5
72	Effect of Stress Engineering on the Electrical Properties of BaTiO3Thin Film. Japanese Journal of Applied Physics, 2011, 50, 09NA03.	1.5	3

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73	Milling Effect of Calcium Aluminate Fine Particle Prepared by Chemical Solution Processing. Journal of the Society of Powder Technology, Japan, 2010, 47, 304-309.	0.1	0
74	Effect of bottom electrode structure on electrical properties of BaTiO3 thin films fabricated by CSD method. Journal of the Ceramic Society of Japan, 2010, 118, 669-673.	1.1	7
75	Enhanced electrical properties of ferroelectric thin films with electric field induced domain control. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 25-28.	3.5	3
76	Preparation of hydroxyapatite–ferrite composite particles by ultrasonic spray pyrolysis. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 195-198.	3.5	42
77	Low-temperature crystallization of CSD-derived PZT thin film with laser annealing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 89-93.	3.5	12
78	Solution derived 12CaO·7Al2O3 thin films on MgO(100) substrate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 21-24.	3.5	6
79	Effect of the electrode structure on the electrical properties of alkoxide derived ferroelectric thin film. Materials Letters, 2010, 64, 1742-1744.	2.6	13
80	Nanostructure and strain analysis of CeO2/YSZ strained superlattice. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 220-228.	3.5	2
81	Comparison of Thermal Stability of Epitaxially Grown (La <sub>0.5</sub> Sr <sub>0.5</sub> )CoO <sub>3</sub> and (La <sub>0.6</sub> Sr <sub>0.4</sub> )MnO <sub>3</sub> Thin Films Deposited on Si Substrate. Key Engineering Materials. 2010. 445. 160-163.	0.4	0
82	Preparation and Characterization of Alkoxide-Derived Lead-Free Piezoelectric Barium Zirconate Titanate Thin Films with Different Compositions. Japanese Journal of Applied Physics, 2010, 49, 09MA11.	1.5	11
83	Preparation of MgIn2O4Epitaxial Oxide Electrode with Spinel Structure and Heteroepitaxial Growth of BaTiO3–NiFe2O4Multiferroic Composite Thin Film. Japanese Journal of Applied Physics, 2009, 48, 09KB06.	1.5	7
84	Low-Frequency Raman Spectroscopy in Pb(Zn <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -PbTiO <sub>3</sub> Mixed Crystals. Ferroelectrics, 2009, 378, 84-91.	0.6	3
85	Oxygen sensitivity of perovskite-type dielectric thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 142-145.	3.5	18
86	Oxygenâ€Enhanced Crystallization of Solutionâ€Derived 12CaO·7Al <sub>2</sub> O <sub>3</sub> . Journal of the American Ceramic Society, 2009, 92, S189.	3.8	5
87	Spray Pyrolysis of Fe3O4-BaTiO3Composite Particles. Journal of the American Ceramic Society, 2009, 92, S177-S180.	3.8	6
88	Valence-EELS analysis of local electronic and optical properties of PMN–PT epitaxial film. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 160-165.	3.5	17
89	Ferroelectric Properties of Epitaxial BiFe <sub>0.9</sub> 7Mn <sub>0.03</sub> O <sub>3</sub> Thin Films with Different Crystal Orientations Deposited on Buffered Si Substrates. Key Engineering Materials, 2009, 421-422, 111-114.	0.4	0
90	Doping effect of Dy on leakage current and oxygen sensing property of SrTiO3 thin film prepared by PLD. Journal of the Ceramic Society of Japan, 2009, 117, 1004-1008.	1.1	3

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91	Stress engineering of the alkoxide derived ferroelectric thin film on Si wafer. Journal of the Ceramic Society of Japan, 2009, 117, 1089-1094.	1.1	27
92	Low-temperature crystallization of CSD-derived PZT thin film with laser assisted annealing. Journal of the Ceramic Society of Japan, 2009, 117, 950-953.	1.1	12
93	Shape controlled ZnO nanoparticle prepared by microwave irradiation method. Journal of the Ceramic Society of Japan, 2009, 117, 961-963.	1.1	4
94	Transition Layer in ZrO2 Ultra-Thin Film by Aberration-corrected TEM. Materia Japan, 2009, 48, 599-599.	0.1	0
95	Thermochromic tungsten doped VO2-SiO2 nano-particle synthesized by chemical solution deposition technique. Journal of the Ceramic Society of Japan, 2009, 117, 970-972.	1.1	8
96	Effect of Back-Etching on Electrical Properties of (111) - oriented PZT thin films. Transactions of the Materials Research Society of Japan, 2009, 34, 113-116.	0.2	0
97	Advantage of the structure and the electrical properties of epitaxial ultra-thin zirconia gate dielectrics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 30-34.	3.5	7
98	Effect of SrTiO3 seed layer deposition time and thickness on low-temperature crystallization and electrical properties of Pb(Zr, Ti)O3 films by metalorganic chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 22-25.	3.5	7
99	Fabrication and optical properties of Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> PbTiO <sub>3</sub> thin films on Si substrates using the PLD method. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2008, 55. 1023-1028.	3.0	15
100	Oxygen Sensing Properties of SrTiO3Thin Films. Japanese Journal of Applied Physics, 2008, 47, 7486-7489.	1.5	23
101	Origin of Compressive Residual Stress in Alkoxide Derived PbTiO3Thin Film on Si Wafer. Japanese Journal of Applied Physics, 2008, 47, 7514-7518.	1.5	13
102	Modification of Ferroelectric Properties of BaTiO3–CoFe2O4Multiferroic Composite Thin Film by Application of Magnetic Field. Japanese Journal of Applied Physics, 2008, 47, 7603-7606.	1.5	19
103	Effect of Back-Etching on Electrical Properties of (001)&(100) Oriented PZT(30/70) Thin Films. Ferroelectrics, 2008, 370, 119-125.	0.6	2
104	Preparation of Epitaxial Pt Bottom Electrode and Tunability of (Ba,Sr)TiO <sub>3</sub> Thin Film Deposited on Si Substrate. Ferroelectrics, 2008, 370, 132-139.	0.6	0
105	Polarized Raman Study in Pb(Zn1/3Nb2/3)O3-PbTiO3Mixed Crystal. Ferroelectrics, 2008, 376, 74-80.	0.6	0
106	Electrooptic Properties of Epitaxial Lead Zirconate Titanate Films on Silicon Substrates. Japanese Journal of Applied Physics, 2007, 46, 6929.	1.5	19
107	Role of SrTiO3 Seed Layer on Low-temperature Crystallization of Pb(Zr, Ti)O3 Films Prepared by Metalorganic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2007, 1034, 7.	0.1	0
108	Effect of Film Thickness on Electrical Properties of Chemical Solution Deposition-Derived Pb(ZrxTi1-x)O3/LaNiO3/Si. Japanese Journal of Applied Physics, 2007, 46, 6925-6928.	1.5	19

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109	Preparation and Structure of Lead Magnesium Niobate Titanate Film by Double-Pulse Excitation using Nd:YAG and KrF Excimer Lasers. Japanese Journal of Applied Physics, 2007, 46, 657-659.	1.5	7
110	Fabrication and Optical Properties of Pb(Mg <inf>1/3</inf> Nb <inf>2/3</inf> )O <inf>3</inf> -PbTiO <inf>3</inf> Thin Films on Si Substrates by PLD Method. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
111	Preparation of AlN thin films by means of CVD using iodide source under atmospheric pressure. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
112	Effect of Source Supply Methods on Low-Temperature Preparation of Lead Zirconate Titanate Thin Films Using SrTiO <sub>3</sub> Seed Layers by Metallorganic Chemical Vapor Deposition. Solid State Phenomena, 2007, 124-126, 153-156.	0.3	3
113	Preparation of InN by Means of AP-HCVD Using In Buffer Layers. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
114	Fabrication of HfO <sub>2</sub> Thin Film on Si Substrate by Double-Pulse Excitation PLD. Key Engineering Materials, 2007, 350, 129-132.	0.4	0
115	Fabrication and Microstructural Change of PMN-PT Thin Films on Si Substrates by PLD with Mask and Double-Pulse Lazer Excitation. Key Engineering Materials, 2007, 350, 111-114.	0.4	6
116	Effect of Oxygen Annealing on Ferroelectricity of BiFeO3Thin Films Formed by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2007, 46, 3491-3494.	1.5	21
117	The effect of SrTiO3 seed and application of in-situ magnetic field on the preparation of Pb(Zr, Ti)O3 thin film by pulsed laser deposition. Transactions of the Materials Research Society of Japan, 2007, 32, 99-104.	0.2	0
118	Room-Temperature Electrical-Field Induced Oxygen Diffusion of Aluminum/Yttria-Stabilized Zirconia Thin Film Grown on Si Substrate. Japanese Journal of Applied Physics, 2006, 45, 8827-8831.	1.5	2
119	Atomic-Scale Structure Investigation of CeO <sub>2</sub> /YSZ/Si Hetero-Interface by High Resolution Analytical Electron Microscope. Bunseki Kagaku, 2006, 55, 419-426.	0.2	0
120	Activation Energy of Oxygen Vacancy Diffusion of Yttria-Stabilized-Zirconia Thin Film Determined from DC Current Measurements below 150 °C. Japanese Journal of Applied Physics, 2006, 45, L525-L528.	1.5	6
121	Electrooptic Properties of Lead Zirconate Titanate Films Prepared on Silicon Substrate. Japanese Journal of Applied Physics, 2006, 45, 7516-7519.	1.5	10
122	Diffusion Behavior at the Interface of (Ba,Sr)TiO <sub>3</sub> (BST)/Electrode/Buffer Layer/Si Epitaxial Multi-Layer Thin Film. Key Engineering Materials, 2006, 301, 257-260.	0.4	0
123	Investigation of Domain Structure and Electrical Properties of Monoclinic Epitaxial Zirconia Buffer Layer. Key Engineering Materials, 2006, 301, 261-264.	0.4	0
124	In Situ Simultaneous Observation of Phase Transition and Electrical Properties of Pb(Zr,Ti)O <sub>3</sub> Thin Film by High Temperature XRD and Electrical Measurement Apparatus. Key Engineering Materials, 2006, 320, 53-56.	0.4	1
125	Preparation of Epitaxial LiTaO <sub>3</sub> Thin Films by Metal Organic Chemical Vapor Deposition and its Electrical and Optical Properties. Key Engineering Materials, 2006, 320, 57-60.	0.4	4
126	Ferroelectricity of BiFeO <sub>3</sub> Thin Films by Pulsed Laser Deposition and Effect of Atmosphere. Key Engineering Materials, 2006, 320, 45-48.	0.4	0

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127	Preparation and Optical Properties of Epitaxial Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -PbTiO <sub>3&lt; Thin Film on Si Substrates with Buffer Layer Using Pulsed Laser Deposition. Key Engineering Materials, 2006, 301, 265-268.</sub>	/sub> 0.4	6
128	Effect on Crystal Orientation on Residual Stress and Electrical Properties of a PZT Thin Film Deposited on Buffered-Si Substrate. Key Engineering Materials, 2006, 320, 65-68.	0.4	1
129	Impact of thin SrTiO3 seed layer to achieve low-temperature crystallization below 300°C and ferroelectricity of lead zirconate titanate thin film. Applied Physics Letters, 2006, 89, 202907.	3.3	24
130	High-resolution TEM Analysis of ZrO <sub>2</sub> Gate Dielectrics Co-doped with Y <sub>2</sub> O <sub>3</sub> Ta <sub>2</sub> O <sub>5</sub> . Materia Japan, 2006, 45, 841-841.	0.1	0
131	High-temperature in situ Cross-sectional Transmission Electron Microscopy Investigation of Crystallization Process of Yttrium-stabilized Zirconia/Si and Yttrium-stabilized Zirconia/SiOx/Si Thin Films. Journal of Materials Research, 2005, 20, 1878-1887.	2.6	5
132	Stress Control and Ferroelectric Properties of Lead Zirconate Titanate (PZT) Thin Film on Si Substrate with Buffer Layers. Japanese Journal of Applied Physics, 2005, 44, 6900-6904.	1.5	17
133	Stress-induced magnetization for epitaxial spinel ferrite filmsthrough interface engineering. Applied Physics Letters, 2004, 85, 1199-1201.	3.3	39
134	Modification of drain current on metal–oxide–semiconductor field-effect transistor by magnetic field induced by remanent magnetization. Applied Physics Letters, 2004, 85, 3772-3774.	3.3	5
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